

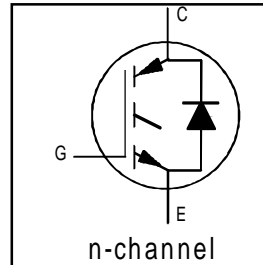
IRG4IBC30KD

INSULATED GATE BIPOLAR TRANSISTOR WITH
ULTRAFAST SOFT RECOVERY DIODE

Short Circuit Rated
UltraFast IGBT

Features

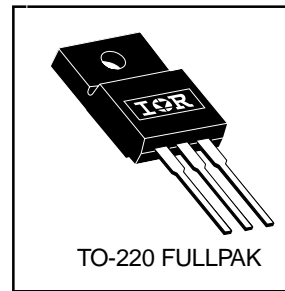
- High switching speed optimized for up to 25kHz with low $V_{CE(on)}$
- Short Circuit Rating $10\mu s$ @ $125^\circ C$, $V_{GE} = 15V$
- Generation 4 IGBT design provides tighter parameter distribution and higher efficiency than previous generation
- IGBT co-packaged with HEXFRED™ ultrafast, ultra-soft-recovery anti-parallel diodes for use in bridge configurations
- Industry standard TO-220 FULLPAK



$V_{CES} = 600V$
 $V_{CE(on) typ.} = 2.21V$
@ $V_{GE} = 15V$, $I_C = 9.2A$

Benefits

- Generation 4 IGBTs offer highest efficiencies available maximizing the power density of the system
- IGBT's optimized for specific application conditions
- HEXFRED™ diodes optimized for performance with IGBTs. Minimized recovery characteristics reduce noise EMI
- Designed to exceed the power handling capability of equivalent industry-standard IGBT



Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	600	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	17	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	9.2	
I_{CM}	Pulsed Collector Current ①⑤	34	
I_{LM}	Clamped Inductive Load Current ②⑤	34	
$I_F @ T_C = 100^\circ C$	Diode Continuous Forward Current	9.2	
I_{FM}	Diode Maximum Forward Current	34	
t_{sc}	Short Circuit Withstand Time	10	μs
V_{ISOL}	RMS Isolation Voltage, Terminal to Case, $t = 1$ min	2500	V
V_{GE}	Gate-to-Emitter Voltage	± 20	W
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	45	
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	18	
T_J	Operating Junction and	-55 to +150	$^\circ C$
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 sec.		
	Mounting Torque, 6-32 or M3 Screw.	10 lbf•in (1.1 N•m)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case - IGBT	—	2.8	$^\circ C/W$
$R_{\theta CS}$	Junction-to-Case - Diode	—	3.7	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	—	65	
Wt	Weight	2.0 (0.07)	—	g (oz)

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Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions	
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage ^③	600	—	—	V	$V_{GE} = 0V, I_C = 250\mu A$	
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.54	—	V/°C	$V_{GE} = 0V, I_C = 1.0mA$	
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	—	2.21	2.7	V	$I_C = 16A$ $I_C = 28A$ $I_C = 16A, T_J = 150^\circ\text{C}$	
		—	2.88	—			$V_{GE} = 15V$
		—	2.36	—			See Fig. 2, 5
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	6.0		$V_{CE} = V_{GE}, I_C = 250\mu A$	
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	—	-12	—	mV/°C	$V_{CE} = V_{GE}, I_C = 250\mu A$	
g_{fe}	Forward Transconductance ^④	5.4	8.1	—	S	$V_{CE} = 100V, I_C = 16A$	
I_{CES}	Zero Gate Voltage Collector Current	—	—	250	μA	$V_{GE} = 0V, V_{CE} = 600V$ $V_{GE} = 0V, V_{CE} = 600V, T_J = 150^\circ\text{C}$	
		—	—	2500			
V_{FM}	Diode Forward Voltage Drop	—	1.4	1.7	V	$I_C = 12A$ $I_C = 12A, T_J = 150^\circ\text{C}$	
		—	1.3	1.6			See Fig. 13
I_{GES}	Gate-to-Emitter Leakage Current	—	—	± 100	nA	$V_{GE} = \pm 20V$	

Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge (turn-on)	—	67	100	nC	$I_C = 16A$ $V_{CC} = 400V$ $V_{GE} = 15V$
Q_{ge}	Gate - Emitter Charge (turn-on)	—	11	16		
Q_{gc}	Gate - Collector Charge (turn-on)	—	25	37		
$t_{d(on)}$	Turn-On Delay Time	—	60	—	ns	$T_J = 25^\circ\text{C}$ $I_C = 16A, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 23\Omega$
t_r	Rise Time	—	42	—		
$t_{d(off)}$	Turn-Off Delay Time	—	160	250		
t_f	Fall Time	—	80	120		
E_{on}	Turn-On Switching Loss	—	0.60	—	mJ	Energy losses include "tail" and diode reverse recovery See Fig. 9,10,14
E_{off}	Turn-Off Switching Loss	—	0.58	—		
E_{ts}	Total Switching Loss	—	1.18	1.6		
t_{sc}	Short Circuit Withstand Time	10	—	—	μs	$V_{CC} = 360V, T_J = 125^\circ\text{C}$ $V_{GE} = 15V, R_G = 10\Omega, V_{CPK} < 500V$
$t_{d(on)}$	Turn-On Delay Time	—	58	—	ns	$T_J = 150^\circ\text{C}$, See Fig. 10,11,18 $I_C = 16A, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 23\Omega$
t_r	Rise Time	—	42	—		
$t_{d(off)}$	Turn-Off Delay Time	—	210	—		
t_f	Fall Time	—	160	—		
E_{ts}	Total Switching Loss	—	1.69	—	mJ	Energy losses include "tail" and diode reverse recovery
L_E	Internal Emitter Inductance	—	7.5	—	nH	Measured 5mm from package
C_{ies}	Input Capacitance	—	920	—	pF	$V_{GE} = 0V$ $V_{CC} = 30V$ $f = 1.0MHz$
C_{oes}	Output Capacitance	—	110	—		
C_{res}	Reverse Transfer Capacitance	—	27	—		
t_{rr}	Diode Reverse Recovery Time	—	42	60	ns	$T_J = 25^\circ\text{C}$ See Fig. 14 $T_J = 125^\circ\text{C}$
		—	80	120		
I_{rr}	Diode Peak Reverse Recovery Current	—	3.5	6.0	A	$T_J = 25^\circ\text{C}$ See Fig. 15 $T_J = 125^\circ\text{C}$
		—	5.6	10		
Q_{rr}	Diode Reverse Recovery Charge	—	80	180	nC	$T_J = 25^\circ\text{C}$ See Fig. 16 $T_J = 125^\circ\text{C}$
		—	220	600		
$di_{(rec)M}/dt$	Diode Peak Rate of Fall of Recovery During t_b	—	180	—	A/ μs	$T_J = 25^\circ\text{C}$ See Fig. 17 $T_J = 125^\circ\text{C}$
		—	160	—		

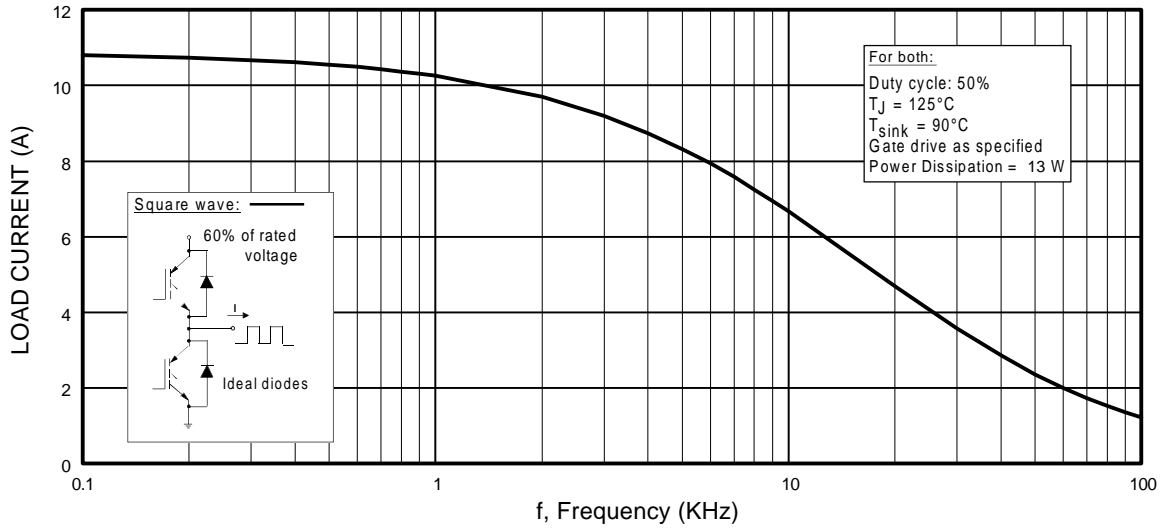


Fig. 1 - Typical Load Current vs. Frequency
 (Load Current = I_{RMS} of fundamental)

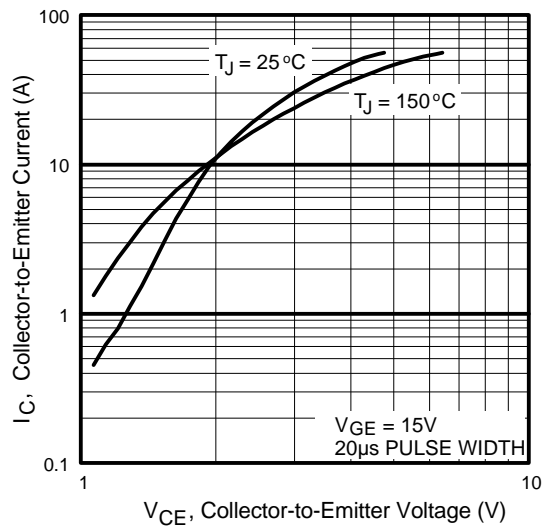


Fig. 2 - Typical Output Characteristics

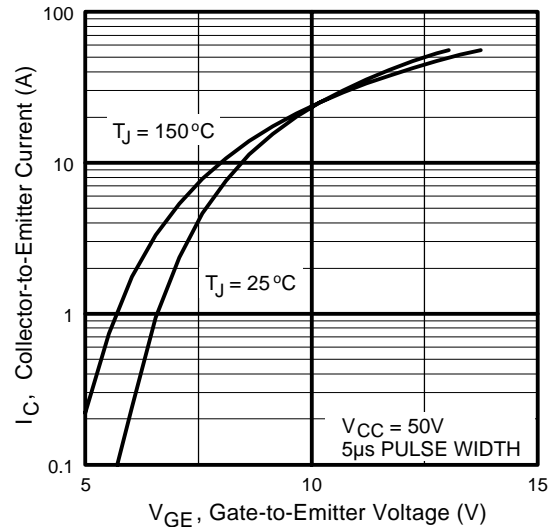


Fig. 3 - Typical Transfer Characteristics

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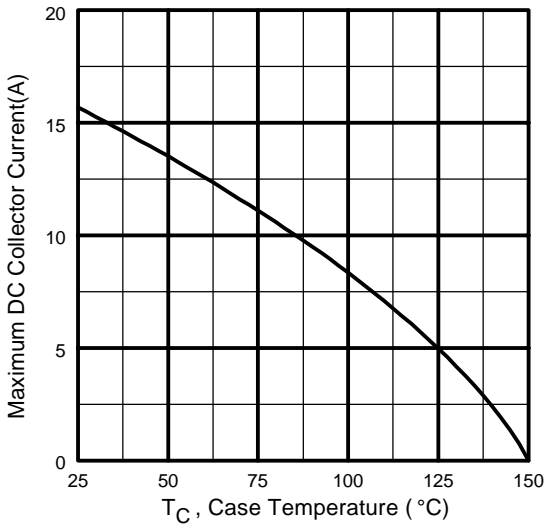


Fig. 4 - Maximum Collector Current vs. Case Temperature

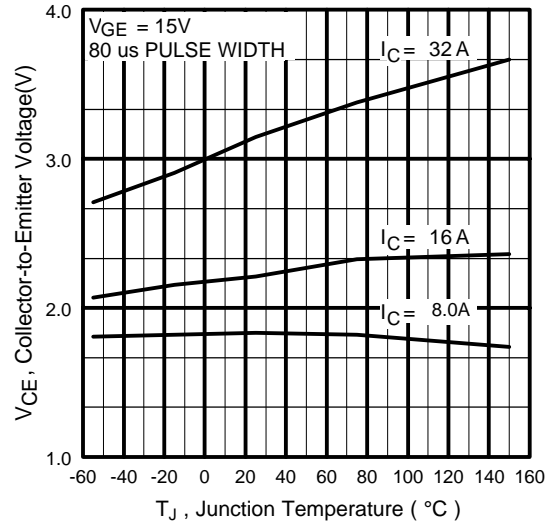


Fig. 5 - Typical Collector-to-Emitter Voltage vs. Junction Temperature

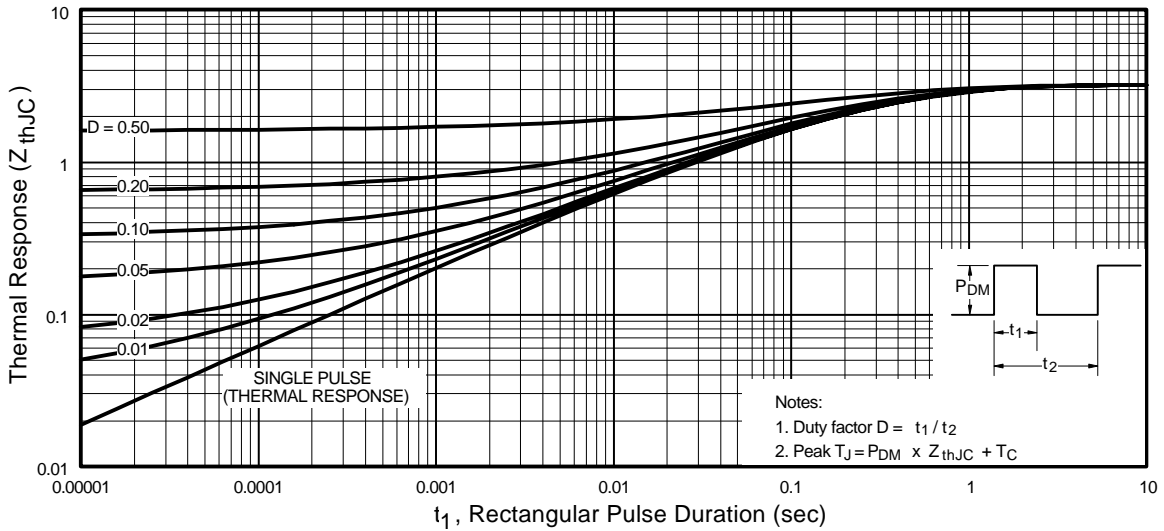


Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

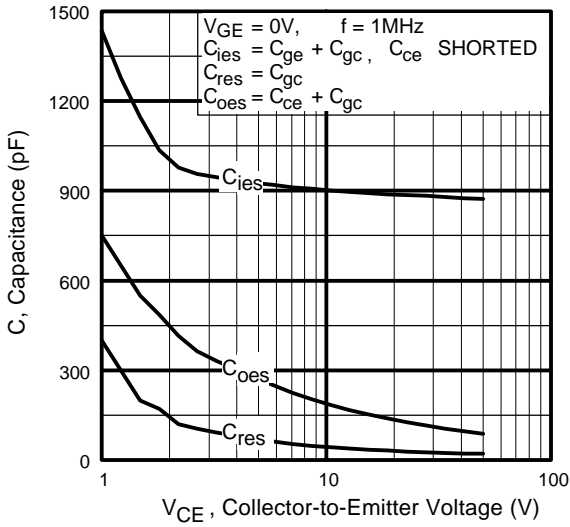


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

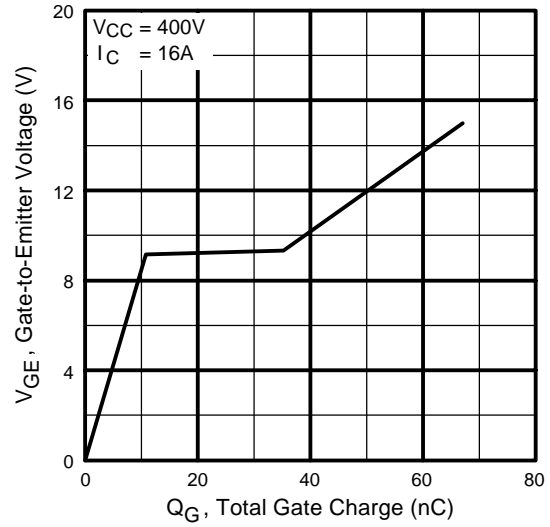


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

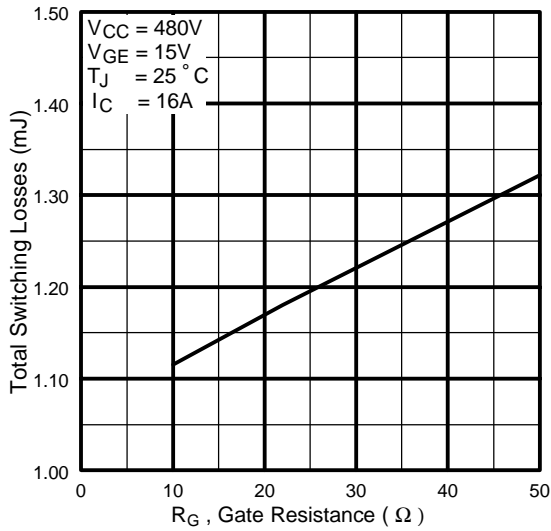


Fig. 9 - Typical Switching Losses vs. Gate Resistance

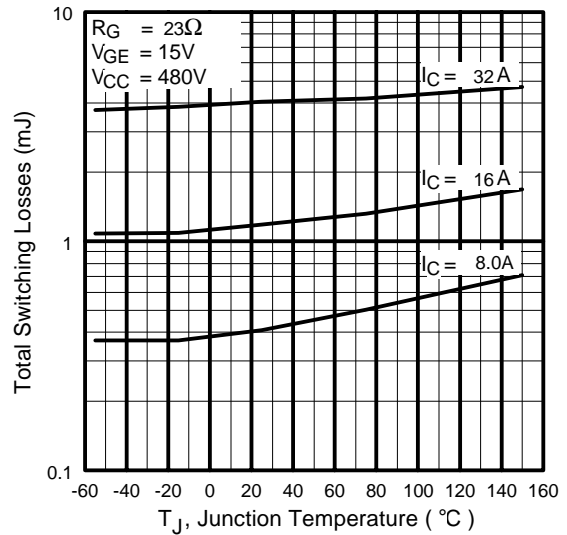


Fig. 10 - Typical Switching Losses vs. Junction Temperature

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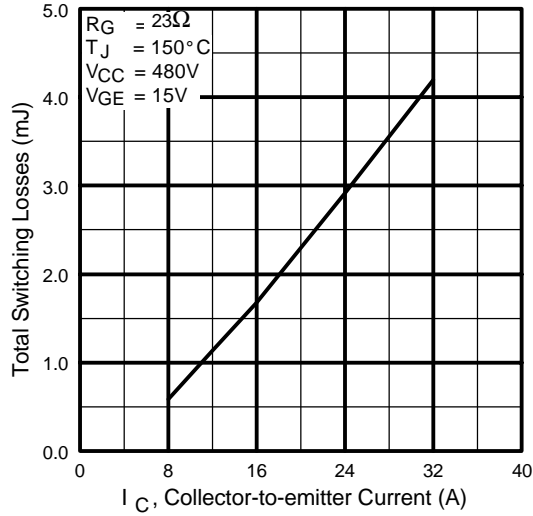


Fig. 11 - Typical Switching Losses vs. Collector-to-Emitter Current

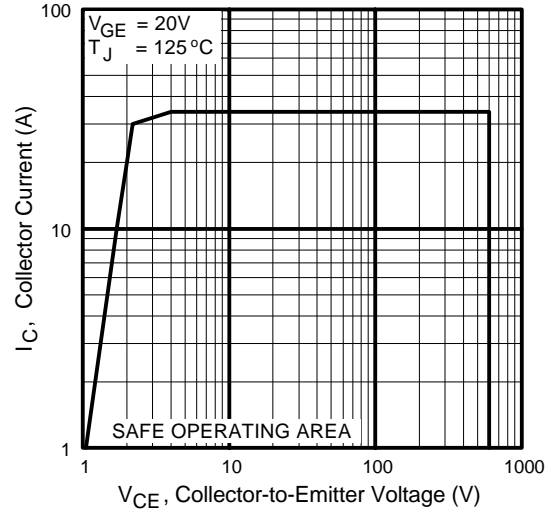


Fig. 12 - Turn-Off SOA

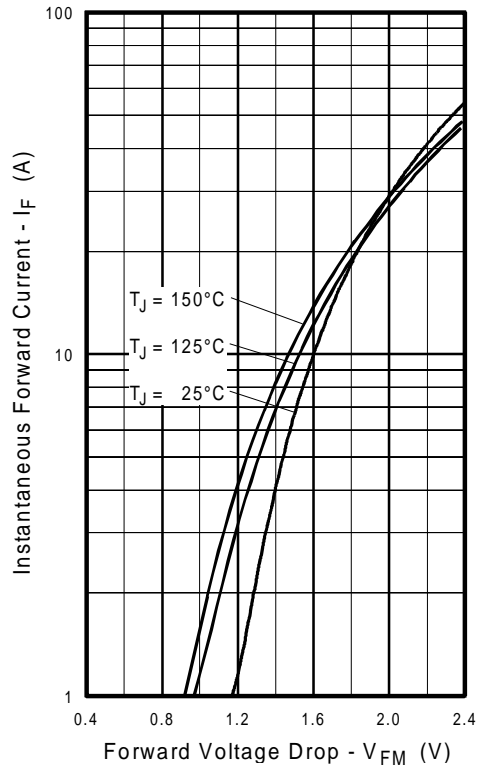


Fig. 13 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

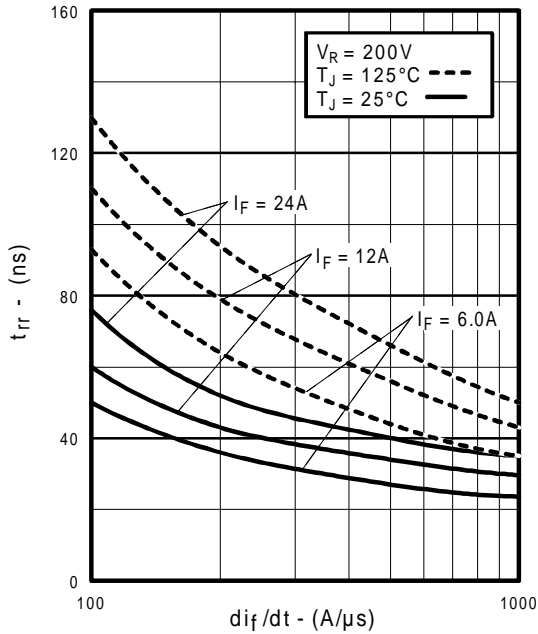


Fig. 14 - Typical Reverse Recovery vs. di_f/dt

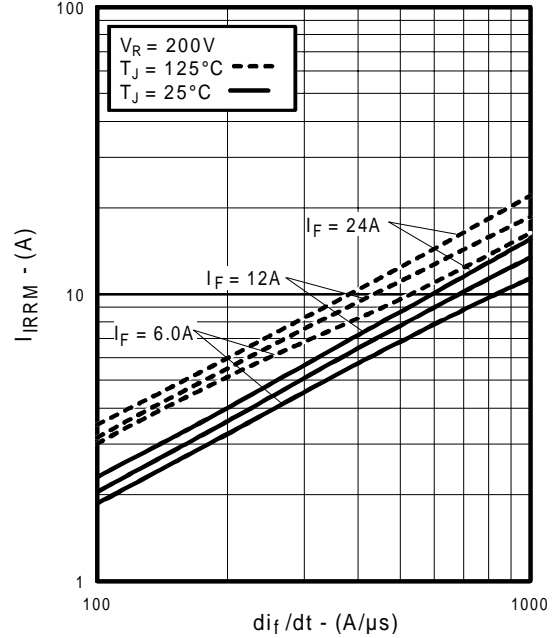


Fig. 15 - Typical Recovery Current vs. di_f/dt



Fig. 16 - Typical Stored Charge vs. di_f/dt

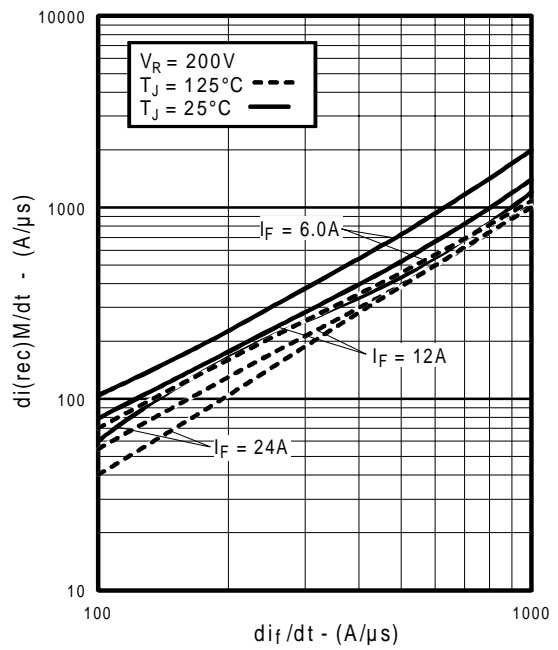


Fig. 17 - Typical $di_{(rec)M}/dt$ vs. di_f/dt

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Fig. 18a - Test Circuit for Measurement of I_{LM} , E_{on} , $E_{off}(\text{diode})$, t_{rr} , Q_{rr} , I_{rr} , $t_{d(on)}$, t_r , $t_{d(off)}$, t_f

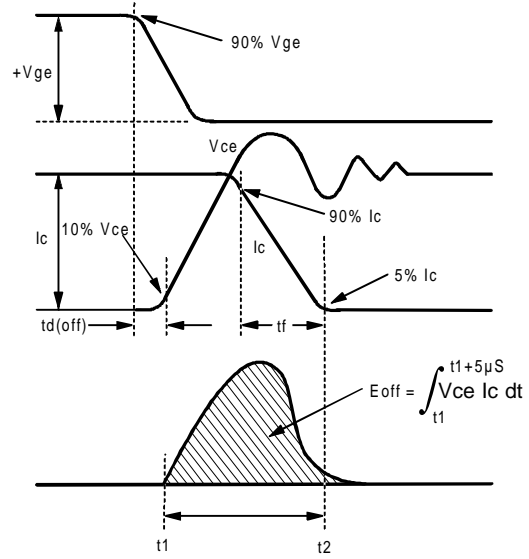


Fig. 18b - Test Waveforms for Circuit of Fig. 18a, Defining E_{off} , $t_{d(off)}$, t_f

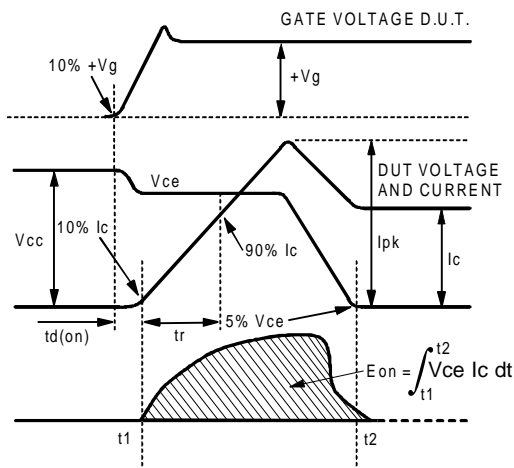


Fig. 18c - Test Waveforms for Circuit of Fig. 18a, Defining E_{on} , $t_{d(on)}$, t_r

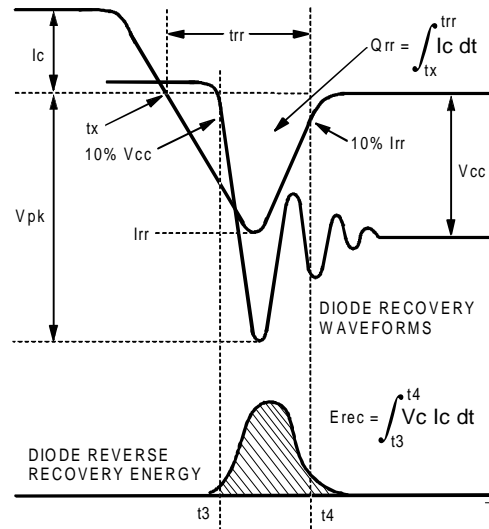


Fig. 18d - Test Waveforms for Circuit of Fig. 18a, Defining E_{rec} , t_{rr} , Q_{rr} , I_{rr}

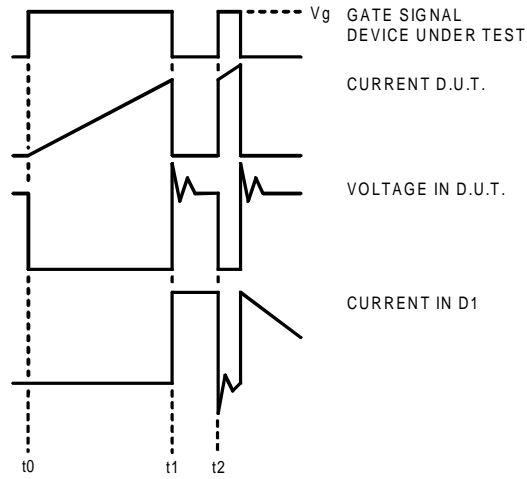


Figure 18e. Macro Waveforms for Figure 18a's Test Circuit

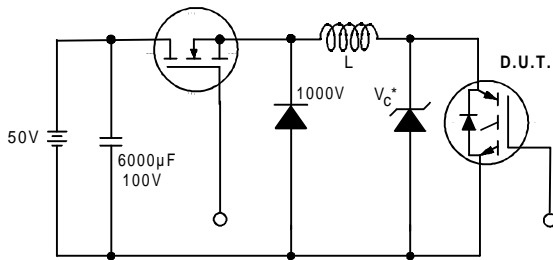


Figure 19. Clamped Inductive Load Test Circuit

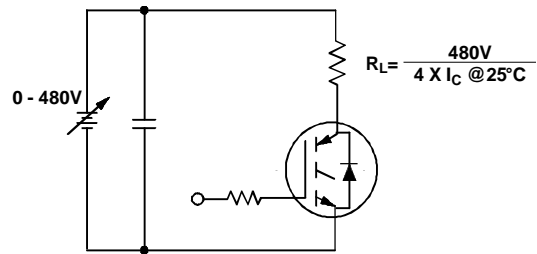


Figure 20. Pulsed Collector Current Test Circuit

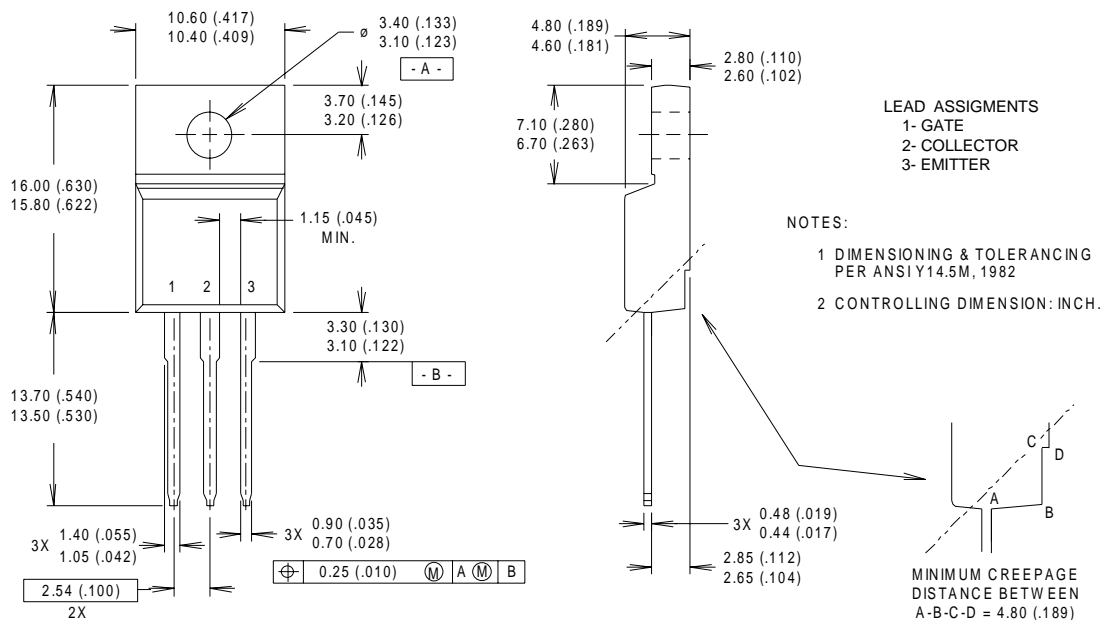
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International
IR Rectifier

Notes:

- ① Repetitive rating: $V_{GE}=20V$; pulse width limited by maximum junction temperature (figure 20)
- ② $V_{CC}=80\%(V_{CES})$, $V_{GE}=20V$, $L=10\mu H$, $R_G=23\Omega$ (figure 19)
- ③ Pulse width $\leq 80\mu s$; duty factor $\leq 0.1\%$.
- ④ Pulse width $5.0\mu s$, single shot.
- ⑤ Uses IRG4BC30KD data and test conditions

Case Outline — TO-220 FULLPAK



International
IR Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
IR EUROPEAN REGIONAL CENTRE: 439/445 Godstone Rd, Whyteleafe, Surrey CR3 0BL, UK Tel: ++ 44 (0)20 8645 8000
IR CANADA: 15 Lincoln Court, Brampton, Ontario L6T3Z2, Tel: (905) 453 2200
IR GERMANY: Saalburgstrasse 157, 61350 Bad Homburg Tel: ++ 49 (0) 6172 96590
IR ITALY: Via Liguria 49, 10071 Borgaro, Torino Tel: ++ 39 011 451 0111
IR JAPAN: K&H Bldg., 2F, 30-4 Nishi-Ikebukuro 3-Chome, Toshima-Ku, Tokyo 171 Tel: 81 (0)3 3983 0086
IR SOUTHEAST ASIA: 1 Kim Seng Promenade, Great World City West Tower, 13-11, Singapore 237994 Tel: ++ 65 (0)838 4630
IR TAIWAN: 16 Fl. Suite D. 207, Sec. 2, Tun Haw South Road, Taipei, 10673 Tel: 886-(0)2 2377 9936
Data and specifications subject to change without notice. 10/00

Note: For the most current drawings please refer to the IR website at:
<http://www.irf.com/package/>